

3FT1N2

主要参数 MAIN CHARACTERISTICS

| | |
|--------------|------|
| $I_{T(RMS)}$ | 1.0A |
| V_{DRM} | 800V |
| I_{GT} | 10mA |

用途

- 交流开关
- 相位控制

产品特性

- 玻璃钝化芯片, 高可靠性和一致性
- 低通态电流和高浪涌电流能力
- 环保 RoHS 产品

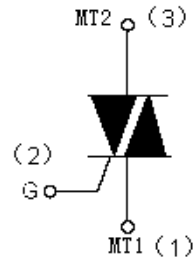
APPLICATIONS

- AC switching
- Phase control

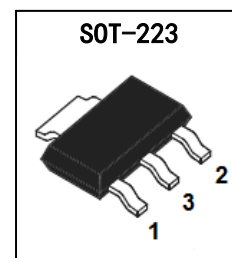
FEATURES

- Glass-passivated mesa chip for high reliability and uniform
- Low on-state voltage and High I_{TSM}
- RoHS products

封装 Package



| 序号 Pin | 引线名称 Description |
|-----------|---------------------|
| 1 | 主电极 1 MT1 |
| 2 | 门极 G |
| 3 | 主电极 2 MT2 |



订货信息 ORDER MESSAGES

| 订货型号 Order codes | | 印记 Marking | 封装 Package |
|------------------|--------------------|---------------|---------------|
| 有卤-编带 | 无卤-编带 | 3FT1N2 | SOT-223 |
| Halogen-Reel | Halogen-Free- Reel | | |
| 3FT1N2-NC-A | 3FT1N2-NC-AR | | |

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^\circ\text{C}$)

| 项 目 Parameter | 符 号 Symbol | 试 验 条 件 Condition | 数 值 Value | 单 位 Unit |
|--|---------------------|--|--------------|------------------------|
| 重复峰值断态电压 Repetitive peak off-state voltage | V_{DRM} | | ± 800 | V |
| 通态方均根电流 On-state RMS current | $I_{\text{T(RMS)}}$ | full sine wave | 1.0 | A |
| 非重复浪涌峰值通态电流 Non-repetitive surge peak on-state current | I_{TSM} | full sine wave , $t=20\text{ms}$ | 10 | A |
| | | full sine wave , $t=16.7\text{ms}$ | 11 | A |
| | I^2t | $t=10\text{ms}$ | 0.5 | A^2s |
| 通态电流临界上升率 Repetitive rate of rise of on-state current after triggering | di/dt | MT1(-),MT2(+),G(+); MT1(-),MT2(+),G(-); MT1(+),MT2(-),G(-) | 50 | $\text{A}/\mu\text{s}$ |
| 峰值门极电流 Peak gate current | I_{GM} | | 2 | A |
| 平均门极功率 Average gate power | $P_{\text{G(AV)}}$ | | 0.5 | W |
| 存储温度 Storage temperature | T_{stg} | | -40~150 | $^\circ\text{C}$ |
| 操作结温 Operation junction temperature | T_{VJ} | | 125 | $^\circ\text{C}$ |



电特性 ELECTRICAL CHARACTERISTIC (T_c=25°C)

| 项 目 Parameter | 符 号 Symbol | 测 试 条 件 Condition | 最小 Min | 典型 Typ | 最大 Max | 单位 Unit |
|--|------------------|--|-----------|-----------|-----------|--------------------|
| 峰值重复断态电流 Peak Repetitive Blocking Current | I _{DRM} | V _{DM} =V _{DRM} , T _j =125°C, gate open | - | - | 0.5 | mA |
| 峰值通态电压 Peak on-state voltage | V _{TM} | I _{TM} =2A | - | - | 1.5 | V |
| 门极触发电流 Gate trigger current | I _{GT} | V _{DM} =12V, R _L =100Ω | - | - | 10 | MT1(-),MT2(+),G(+) |
| | | | | | | MT1(-),MT2(+),G(-) |
| | | | | | | MT1(+),MT2(-),G(-) |
| | | | | | | MT1(+),MT2(-),G(+) |
| 门极触发电压 Gate trigger voltage | V _{GT} | V _{DM} =12V,R _L =100Ω | - | - | 1.5 | V |
| 维持电流 Holding current | I _H | V _{DM} =12V, I _{GT} =0.1A | - | - | 15 | mA |
| 擎住电流 Latching current | I _L | V _{DM} =12V, I _{GT} =0.1A | - | - | 20 | mA |
| 断态临界电压上升率 Rise of off- state voltage | dV/dt | V _{DM} =67% V _{DRM(MAX)} , T _j =125°C, gate open | - | 30 | - | V/μs |

热特性 THERMAL CHARACTERISTIC

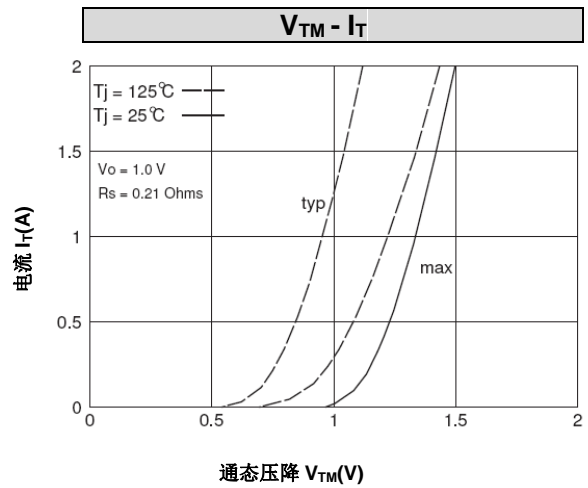
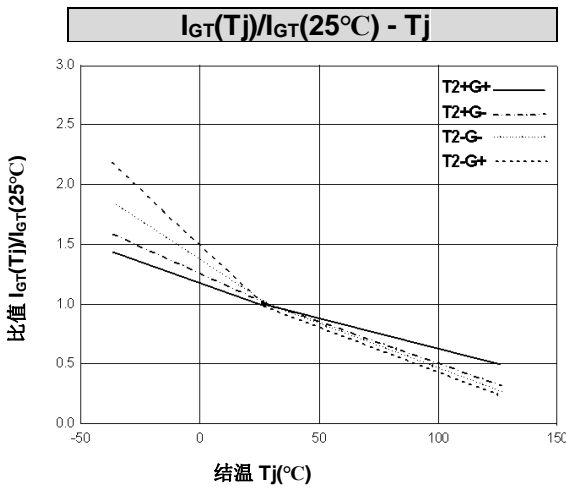
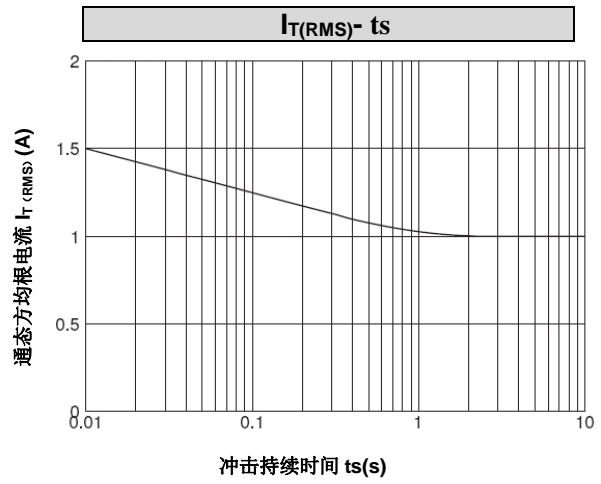
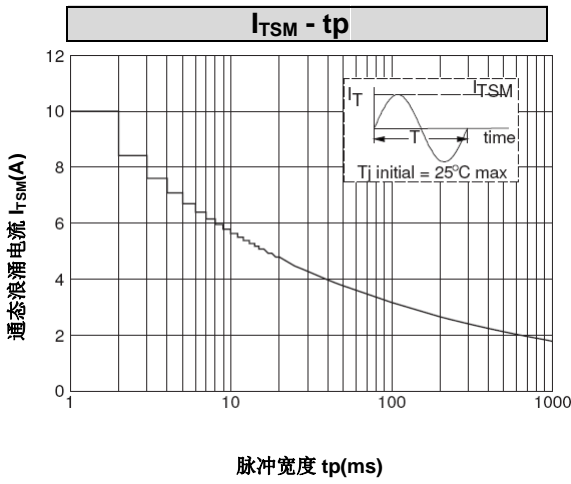
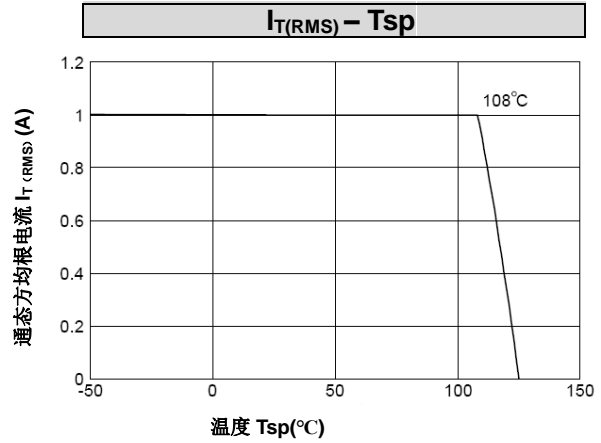
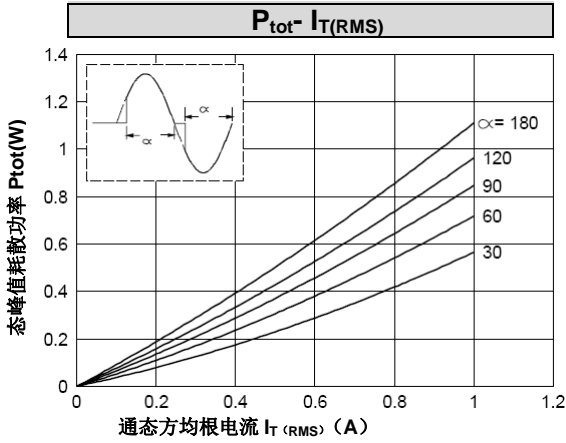
| 项 目 Parameter | 符 号 Symbol | 条 件 Condition | 最小 Min | 典型 Typ | 最大 Max | 单位 Unit |
|---|-----------------------|----------------------|-----------|-----------|-----------|------------|
| 结到引线的热阻 Thermal resistance junction to solder point | R _{th(j-sp)} | full cycle (SOT-223) | - | - | 15 | °C/W |

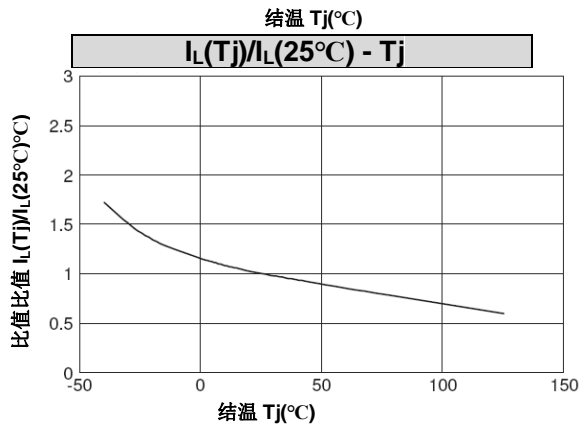
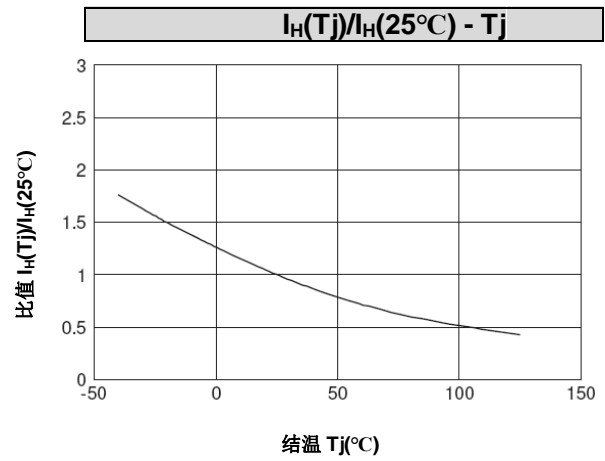
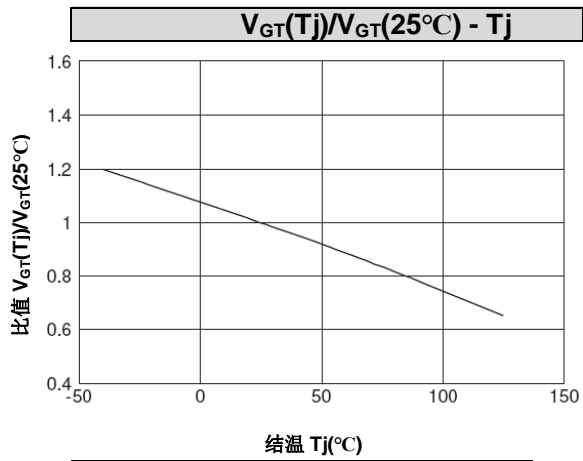




特征曲线 ELECTRICAL CHARACTERISTICS (curves)

特征曲线 ELECTRICAL CHARACTERISTICS (curves)





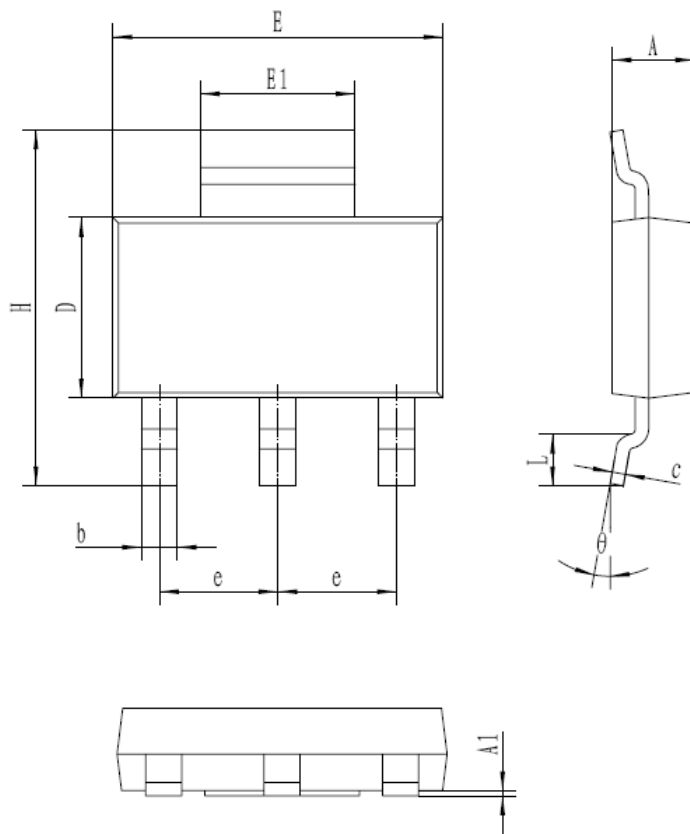


3FT1N2

外形尺寸 PACKAGE MECHANICAL DATA

SOT-223

单位 Unit : mm



| symbol 符号 | MIN | MAX |
|--------------|-----------|------|
| A | 1.50 | 1.70 |
| A1 | 0.02 | 0.10 |
| b | 0.60 | 0.80 |
| c | 0.24 | 0.31 |
| D | 3.30 | 3.70 |
| E | 6.30 | 6.50 |
| E1 | 2.90 | 3.10 |
| e | 2.30 TYPE | |
| H | 6.75 | 7.05 |
| L | 0.8 | 1.20 |
| θ | 0° | 10° |



**注意事项**

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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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